

Douglas J Paul

List of Publications by Year in descending order

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291
papers

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294
all docs

294
docs citations

294
times ranked

5151
citing authors

#	ARTICLE	IF	CITATIONS
1	Si/SiGe heterostructures: from material and physics to devices and circuits. Semiconductor Science and Technology, 2004, 19, R75-R108.	2.0	485
2	Design and fabrication of memory devices based on nanoscale polyoxometalate clusters. Nature, 2014, 515, 545-549.	27.8	301
3	Measurement of the Earth tides with a MEMS gravimeter. Nature, 2016, 531, 614-617.	27.8	237
4	Midinfrared Plasmon-Enhanced Spectroscopy with Germanium Antennas on Silicon Substrates. Nano Letters, 2015, 15, 7225-7231.	9.1	173
5	Intersubband electroluminescence from Si/SiGe cascade emitters at terahertz frequencies. Applied Physics Letters, 2002, 81, 1543-1545.	3.3	130
6	Silicon-Germanium Strained Layer Materials in Microelectronics. Advanced Materials, 1999, 11, 191-204.	21.0	126
7	Ge-on-Si Single-Photon Avalanche Diode Detectors: Design, Modeling, Fabrication, and Characterization at Wavelengths 1310 and 1550 nm. IEEE Transactions on Electron Devices, 2013, 60, 3807-3813.	3.0	116
8	High performance planar germanium-on-silicon single-photon avalanche diode detectors. Nature Communications, 2019, 10, 1086.	12.8	104
9	Tunability of the dielectric function of heavily doped germanium thin films for mid-infrared plasmonics. Physical Review B, 2016, 94, .	3.2	86
10	Ohmic contacts to n-type germanium with low specific contact resistivity. Applied Physics Letters, 2012, 100, .	3.3	83
11	High-performance nMOSFETs using a novel strained Si/SiGe CMOS architecture. IEEE Transactions on Electron Devices, 2003, 50, 1961-1969.	3.0	81
12	Facile Surfactant-Free Synthesis of p-Type SnSe Nanoplates with Exceptional Thermoelectric Power Factors. Angewandte Chemie - International Edition, 2016, 55, 6433-6437.	13.8	81
13	The progress towards terahertz quantum cascade lasers on silicon substrates. Laser and Photonics Reviews, 2010, 4, 610-632.	8.7	79
14	8-band k -modeling of the quantum confined Stark effect in Ge quantum wells on Si substrates. Physical Review B, 2008, 77, .	3.2	77
15	Roadmap for the next-generation of hybrid photovoltaic-thermal solar energy collectors. Solar Energy, 2018, 174, 386-398.	6.1	77
16	Interwell intersubband electroluminescence from Si/SiGe quantum cascade emitters. Applied Physics Letters, 2003, 83, 4092-4094.	3.3	74
17	Nanofabrication of high aspect ratio ($\sim 1/450:1$) sub-100nm silicon nanowires using inductively coupled plasma etching. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	73
18	Silicon as a model ion trap: Time domain measurements of donor Rydberg states. Proceedings of the National Academy of Sciences of the United States of America, 2008, 105, 10649-10653.	7.1	71

#	ARTICLE	IF	CITATIONS
19	Silicon germanium heterostructures in electronics: the present and the future. <i>Thin Solid Films</i> , 1998, 321, 172-180.	1.8	70
20	Mid-infrared emissivity of crystalline silicon solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2018, 174, 607-615.	6.2	68
21	Physics and Applications of Terahertz Radiation. Springer Series in Optical Sciences, 2014, , .	0.7	66
22	The thermoelectric properties of Ge/SiGe modulation doped superlattices. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	65
23	Chlorine-Enabled Electron Doping in Solution-Synthesized SnSe Thermoelectric Nanomaterials. <i>Advanced Energy Materials</i> , 2017, 7, 1602328.	19.5	64
24	Low loss Ge-on-Si waveguides operating in the 8-14 μm atmospheric transmission window. <i>Optics Express</i> , 2018, 26, 25667.	3.4	56
25	Optical Activation of Germanium Plasmonic Antennas in the Mid-Infrared. <i>Physical Review Letters</i> , 2016, 117, 047401.	7.8	55
26	High performance Si/Si _{1-x} Ge _x resonant tunneling diodes. <i>IEEE Electron Device Letters</i> , 2001, 22, 182-184.	3.9	53
27	ITO and AZO films for low emissivity coatings in hybrid photovoltaic-thermal applications. <i>Solar Energy</i> , 2017, 155, 82-92.	6.1	51
28	The cross-plane thermoelectric properties of p-Ge/Si _{0.5} Ge _{0.5} superlattices. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	47
29	Room temperature operation of <i>n</i> -type Ge/SiGe terahertz quantum cascade lasers predicted by non-equilibrium Green's functions. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	45
30	3D LIDAR imaging using Ge-on-Si single-photon avalanche diode detectors. <i>Optics Express</i> , 2020, 28, 1330.	3.4	45
31	A study of the impact of dislocations on the thermoelectric properties of quantum wells in the Si/SiGe materials system. <i>Journal of Applied Physics</i> , 2011, 110, .	2.5	44
32	Plasmonic mid-infrared third harmonic generation in germanium nanoantennas. <i>Light: Science and Applications</i> , 2018, 7, 106.	16.6	42
33	Si/SiGe electron resonant tunneling diodes. <i>Applied Physics Letters</i> , 2000, 77, 1653-1655.	3.3	39
34	Picosecond intersubband dynamics in p-Si/SiGe quantum-well emitter structures. <i>Applied Physics Letters</i> , 2002, 80, 1456-1458.	3.3	39
35	The scaled performance of Si/Si _{1-x} Ge _x resonant tunneling diodes. <i>IEEE Electron Device Letters</i> , 2001, 22, 582-584.	3.9	38
36	Analysis of Ge micro-cavities with in-plane tensile strains above 2 %. <i>Optics Express</i> , 2016, 24, 4365.	3.4	38

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37	High-mobility two-dimensional electron gases in Si/SiGe heterostructures on relaxed SiGe layers grown at high temperature. <i>Semiconductor Science and Technology</i> , 1997, 12, 943-946.	2.0	36
38	Coulomb blockade in silicon based structures at temperatures up to 50 K. <i>Applied Physics Letters</i> , 1993, 63, 631-632.	3.3	35
39	Mid-infrared light emission > 3 Åm wavelength from tensile strained GeSn microdisks. <i>Optics Express</i> , 2017, 25, 25374.	3.4	34
40	Study of Single- and Dual-Channel Designs for High-Performance Strained-SiGe n-MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2004, 51, 1245-1253.	3.0	33
41	Interwell relaxation times in SiGe asymmetric quantum well structures: Role of interface roughness. <i>Physical Review B</i> , 2007, 75, .	3.2	32
42	Determination of complex refractive index of thin metal films from terahertz time-domain spectroscopy. <i>Journal of Applied Physics</i> , 2008, 104, .	2.5	32
43	Silicon photonics: a bright future?. <i>Electronics Letters</i> , 2009, 45, 582.	1.0	31
44	One dimensional transport in silicon nanowire junction-less field effect transistors. <i>Scientific Reports</i> , 2017, 7, 3004.	3.3	31
45	Benchmarking the Use of Heavily Doped Ge for Plasmonics and Sensing in the Mid-Infrared. <i>ACS Photonics</i> , 2018, 5, 3601-3607.	6.6	31
46	Toward Silicon-Based Lasers for Terahertz Sources. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2006, 12, 1570-1578.	2.9	30
47	Thin SiGe virtual substrates for Ge heterostructures integration on silicon. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	28
48	Optical properties of highly n-doped germanium obtained by <i>in situ</i> doping and laser annealing. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 465103.	2.8	28
49	Field Tests of a Portable MEMS Gravimeter. <i>Sensors</i> , 2017, 17, 2571.	3.8	28
50	Topotactic anion-exchange in thermoelectric nanostructured layered tin chalcogenides with reduced selenium content. <i>Chemical Science</i> , 2018, 9, 3828-3836.	7.4	28
51	Two-dimensional electron gas mobility as a function of virtual substrate quality in strained Si/SiGe heterojunctions. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998, 16, 1634.	1.6	27
52	Temperature dependence of terahertz optical transitions from boron and phosphorus dopant impurities in silicon. <i>Applied Physics Letters</i> , 2005, 87, 101114.	3.3	27
53	Group-IV midinfrared plasmonics. <i>Journal of Nanophotonics</i> , 2015, 9, 093789.	1.0	27
54	Intersubband lifetimes in SiGe terahertz quantum cascade heterostructures. <i>Physical Review B</i> , 2005, 71, .	3.2	26

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55	Electrical properties of two-dimensional electron gases grown on cleaned SiGe virtual substrates. Thin Solid Films, 1998, 321, 181-185.	1.8	25
56	Si-based electroluminescence at THz frequencies. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 10-12.	3.5	25
57	Ge/SiGe quantum confined Stark effect electro-absorption modulation with low voltage swing at $\lambda = 1550$ nm. Optics Express, 2014, 22, 19284.	3.4	25
58	Determining the Electronic Performance Limitations in Top-Down-Fabricated Si Nanowires with Mean Widths Down to 4 nm. Nano Letters, 2014, 14, 6056-6060.	9.1	25
59	Extending the emission wavelength of Ge nanopillars to 225 nm using silicon nitride stressors. Optics Express, 2015, 23, 18193.	3.4	25
60	Control of Electron-State Coupling in Asymmetric Ge/Si Quantum Wells. Physical Review Applied, 2019, 11, .	3.8	25
61	Silicon germanium makes its mark. Physics World, 2000, 13, 27-32.	0.0	24
62	Ge/SiGe superlattices for thermoelectric energy conversion devices. Journal of Materials Science, 2013, 48, 2829-2835.	3.7	23
63	A novel absorptive/reflective solar concentrator for heat and electricity generation: An optical and thermal analysis. Energy Conversion and Management, 2016, 114, 142-153.	9.2	23
64	Mid-infrared intersubband absorption from p-Ge quantum wells grown on Si substrates. Applied Physics Letters, 2016, 108, .	3.3	22
65	Low temperature characterization of modulation doped SiGe grown on bonded silicon insulator. Applied Physics Letters, 1996, 69, 2704-2706.	3.3	21
66	Relative importance of the electron interaction strength and disorder in the two-dimensional metallic state. Physical Review B, 2002, 66, .	3.2	21
67	Si/SiGe quantum cascade superlattice designs for terahertz emission. Journal of Applied Physics, 2010, 107, 053109.	2.5	21
68	Prospects for SiGe thermoelectric generators. Solid-State Electronics, 2014, 98, 70-74.	1.4	21
69	Multiphysics Simulations of a Thermoelectric Generator. Energy Procedia, 2015, 75, 633-638.	1.8	21
70	Ultra-broadband mid-infrared Ge-on-Si waveguide polarization rotator. APL Photonics, 2020, 5, 026102.	5.7	21
71	1.55 μ m direct bandgap electroluminescence from strained n-Ge quantum wells grown on Si substrates. Applied Physics Letters, 2012, 101, .	3.3	19
72	High sensitivity Ge-on-Si single-photon avalanche diode detectors. Optics Letters, 2020, 45, 6406.	3.3	19

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73	1.4 million Q factor Si ₃ N ₄ micro-ring resonator at 780nm wavelength for chip-scale atomic systems. Optics Express, 2020, 28, 4010.	3.4	18
74	Sub-megahertz linewidth 780.24nm distributed feedback laser for ⁸⁷ Rb applications. Optics Letters, 2020, 45, 3529.	3.3	18
75	Silicon nitride waveguide polarization rotator and polarization beam splitter for chip-scale atomic systems. APL Photonics, 2022, 7, .	5.7	18
76	On-chip infrared photonics with Si-Ge-heterostructures: What is next?. APL Photonics, 2022, 7, .	5.7	18
77	Si/SiGe quantum-cascade emitters for terahertz applications. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 147-155.	2.7	17
78	Ba ₆ Nd ₈ Ti ₁₈ O ₅₄ Tungsten Bronze: A New High-Temperature n-Type Oxide Thermoelectric. Journal of Electronic Materials, 2016, 45, 1894-1899.	2.2	17
79	Experimental and Simulation Study of Silicon Nanowire Transistors Using Heavily Doped Channels. IEEE Nanotechnology Magazine, 2017, 16, 727-735.	2.0	17
80	Ge/SiGe superlattices for nanostructured thermoelectric modules. Thin Solid Films, 2013, 543, 153-156.	1.8	16
81	Interfacial sharpness and intermixing in a Ge-SiGe multiple quantum well structure. Journal of Applied Physics, 2018, 123, .	2.5	16
82	Silicon quantum integrated circuits – an attempt to fabricate silicon-based quantum devices using CMOS fabrication techniques. Thin Solid Films, 1998, 336, 130-136.	1.8	15
83	8-band k·p modelling of mid-infrared intersubband absorption in Ge quantum wells. Journal of Applied Physics, 2016, 120, .	2.5	15
84	THz intersubband electroluminescence from n-type Ge/SiGe quantum cascade structures. Applied Physics Letters, 2021, 118, .	3.3	15
85	Disentangling nonradiative recombination processes in Ge micro-crystals on Si substrates. Applied Physics Letters, 2016, 108, .	3.3	14
86	A High Stability Optical Shadow Sensor With Applications for Precision Accelerometers. IEEE Sensors Journal, 2018, 18, 4108-4116.	4.7	14
87	Field-resolved detection of the temporal response of a single plasmonic antenna in the mid-infrared. Optica, 2021, 8, 898.	9.3	14
88	Low-Loss Surface-Mode Waveguides for Terahertz Si/SiGe Quantum Cascade Lasers. IEEE Journal of Quantum Electronics, 2006, 42, 1233-1238.	1.9	13
89	Cotunneling of holes in silicon-based structures. Physical Review B, 1994, 49, 16514-16517.	3.2	12
90	Terahertz absorption-saturation and emission from electron-doped germanium quantum wells. Optics Express, 2020, 28, 7245.	3.4	12

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91	Si ^{1-x} Ge ^x pulsed plasma etching using CHF ₃ and H ₂ . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2234.	1.6	11
92	Schottky gating high mobility Si/Si ^{1-x} Ge ^x 2D electron systems. Thin Solid Films, 2000, 369, 316-319.	1.8	11
93	Si/SiGe electron resonant tunneling diodes with graded spacer wells. Applied Physics Letters, 2001, 78, 4184-4186.	3.3	11
94	SPICE Modeling of the Scaling of Resonant Tunneling Diodes and the Effects of Sidewall Leakage. IEEE Transactions on Electron Devices, 2012, 59, 3555-3560.	3.0	11
95	Microelectromechanical system gravimeters as a new tool for gravity imaging. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2018, 376, 20170291.	3.4	11
96	THz Bolometer Detectors. Springer Series in Optical Sciences, 2014, , 35-75.	0.7	11
97	Design and simulation of losses in Ge/SiGe terahertz quantum cascade laser waveguides. Optics Express, 2020, 28, 4786.	3.4	11
98	n-type Si/SiGe resonant tunnelling diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 26-29.	3.5	10
99	Transverse resistance overshoot in a Si/SiGe two-dimensional electron gas in the quantum Hall effect regime. Europhysics Letters, 2005, 69, 997-1002.	2.0	10
100	Ge/SiGe Superlattices for Thermoelectric Devices Grown by Low-Energy Plasma-Enhanced Chemical Vapor Deposition. Journal of Electronic Materials, 2013, 42, 2030-2034.	2.2	10
101	Coupled Simulation of Performance of a Crossed Compound Parabolic Concentrator with Solar Cell. Energy Procedia, 2015, 75, 325-330.	1.8	10
102	The UK National Quantum Technologies Hub in sensors and metrology (Keynote Paper). Proceedings of SPIE, 2016, , .	0.8	10
103	Strain analysis of a Ge micro disk using precession electron diffraction. Journal of Applied Physics, 2019, 126, .	2.5	10
104	Ge-on-Si single-photon avalanche diode detectors for short-wave infrared wavelengths. JPhys Photonics, 2022, 4, 012001.	4.6	10
105	Electrical properties and uniformity of two dimensional electron gases grown on cleaned SiGe virtual substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1644.	1.6	9
106	Evidence for multiple impurity bands in sodium-doped silicon MOSFETs. Physical Review B, 2006, 73, .	3.2	9
107	Thermal Conductivity Measurement Methods for SiGe Thermoelectric Materials. Journal of Electronic Materials, 2013, 42, 2376-2380.	2.2	9
108	Principles and Applications of THz Time Domain Spectroscopy. Springer Series in Optical Sciences, 2014, , 203-231.	0.7	9

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109	Silver antimony Ohmic contacts to moderately doped n-type germanium. Applied Physics Letters, 2014, 104, .	3.3	9
110	Beyond Moore's law. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2014, 372, 20130376.	3.4	9
111	Facile Surfactant-Free Synthesis of p-Type SnSe Nanoplates with Exceptional Thermoelectric Power Factors. Angewandte Chemie, 2016, 128, 6543-6547.	2.0	9
112	Thermal emissivity of silicon heterojunction solar cells. Solar Energy Materials and Solar Cells, 2019, 201, 110051.	6.2	9
113	Characterization of integrated waveguides by atomic-force-microscopy-assisted mid-infrared imaging and spectroscopy. Optics Express, 2020, 28, 22186.	3.4	9
114	Pump-probe measurement of lifetime engineering in SiGe quantum wells below the optical phonon energy. Semiconductor Science and Technology, 2005, 20, L50-L52.	2.0	8
115	Si-SiGe n-type resonant tunneling diodes fabricated using in situ hydrogen cleaning. Applied Physics Letters, 2007, 90, 203501.	3.3	8
116	Fabrication of mid-infrared plasmonic antennas based on heavily doped germanium thin films. Thin Solid Films, 2016, 602, 52-55.	1.8	8
117	A Portable MEMS Gravimeter for the Detection of the Earth Tides. , 2018, , .		8
118	Ge-on-Si waveguides for sensing in the molecular fingerprint regime. Optics Express, 2020, 28, 5749.	3.4	8
119	SiGe quantum cascade structures for light emitting devices. Journal of Crystal Growth, 2005, 278, 488-494.	1.5	7
120	Activation mechanisms in sodium-doped silicon MOSFETs. Journal of Physics Condensed Matter, 2007, 19, 226216.	1.8	7
121	Power Factor Characterization of Ge/SiGe Thermoelectric Superlattices at 300K. Journal of Electronic Materials, 2013, 42, 1449-1453.	2.2	7
122	Impact of Randomly Distributed Dopants on Ω -Gate Junctionless Silicon Nanowire Transistors. IEEE Transactions on Electron Devices, 2018, 65, 1692-1698.	3.0	7
123	Masking by weak localization of metallic behavior in a two-dimensional electron system in strong parallel magnetic fields. Physical Review B, 2004, 69, .	3.2	6
124	A Review of Progress Towards Terahertz Si/SiGe Quantum Cascade Lasers. IETE Journal of Research, 2007, 53, 285-292.	2.6	6
125	Fabrication of wires in silicon germanium material. Microelectronic Engineering, 1993, 21, 349-352.	2.4	5
126	Gating high mobility silicon-germanium heterostructures. Microelectronic Engineering, 1997, 35, 309-312.	2.4	5

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127	Electroluminescence from Si/SiGe quantum cascade emitters. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 16, 309-314.	2.7	5
128	Longitudinal conductivity in Si/SiGe heterostructure at integer filling factors. <i>Physical Review B</i> , 2003, 68, .	3.2	5
129	Electron effective mass in ultrathin oxide silicon MOSFET inversion layers. <i>Semiconductor Science and Technology</i> , 2005, 20, 664-667.	2.0	5
130	Strained germanium nanostructures on silicon emitting at $\approx 2.2 \mu\text{m}$ wavelength. , 2013, , .		5
131	Low Specific Ohmic Contacts to n-type Germanium Using a Low Temperature NiGe Process. <i>ECS Transactions</i> , 2013, 50, 1081-1084.	0.5	5
132	Mid-infrared plasmonic platform based on heavily doped epitaxial Ge-on-Si: Retrieving the optical constants of thin Ge epilayers. , 2014, , .		5
133	Multilayered Ge/SiGe Material in Microfabricated Thermoelectric Modules. <i>Journal of Electronic Materials</i> , 2014, 43, 3838-3843.	2.2	5
134	Scalable solar thermoelectrics and photovoltaics (SUNTRAP). <i>AIP Conference Proceedings</i> , 2016, , .	0.4	5
135	n-Ge on Si for mid-infrared plasmonic sensors. , 2017, , .		5
136	Quantum interference in silicon one-dimensional junctionless nanowire field-effect transistors. <i>Physical Review B</i> , 2018, 98, .	3.2	5
137	Electron Population Dynamics in Optically Pumped Asymmetric Coupled Ge/SiGe Quantum Wells: Experiment and Models. <i>Photonics</i> , 2020, 7, 2.	2.0	5
138	High efficiency planar geometry germanium-on-silicon single-photon avalanche diode detectors. , 2020, , .		5
139	Integrated DFB Lasers on Si ₃ N ₄ Photonic Platform for Chip-Scale Atomic Systems. , 2019, , .		5
140	Investigations of electron-beam and optical induced damage in high mobility SiGe heterostructures. <i>Solid-State Electronics</i> , 1997, 41, 1509-1513.	1.4	4
141	Cyclotron resonance measurements of Si/SiGe two-dimensional electron gases with differing strain. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998, 16, 1655.	1.6	4
142	Si/Si _{1-x} Ge _x heterostructure field effect transistors fabricated using a low thermal budget CMOS process. <i>Microelectronic Engineering</i> , 2000, 53, 209-212.	2.4	4
143	THz intersubband dynamics in p-Si/SiGe quantum well structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 904-907.	2.7	4
144	Terahertz Emission From Silicon-Germanium Quantum Cascades. , 2003, , 367-382.		4

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145	Optical cavities for Si/SiGe terahertz quantum cascade emitters. <i>Optical Materials</i> , 2005, 27, 851-854.	3.6	4
146	Low-temperature molecular beam epitaxy growth of Si/SiGe THz quantum cascade structures on virtual substrates. <i>Thin Solid Films</i> , 2006, 508, 24-28.	1.8	4
147	Magnetoconductivity of Hubbard bands induced in silicon MOSFETs. <i>Physica B: Condensed Matter</i> , 2007, 400, 218-223.	2.7	4
148	Si/SiGe Bound-to-Continuum Quantum Cascade Emitters. <i>ECS Transactions</i> , 2009, 16, 865-874.	0.5	4
149	(Invited) Germanium/Silicon Heterostructures for Terahertz Emission. <i>ECS Transactions</i> , 2013, 50, 763-771.	0.5	4
150	Thermoelectric cross-plane properties on p- and n-Ge/SixGe1-x superlattices. <i>Thin Solid Films</i> , 2016, 602, 90-94.	1.8	4
151	GaAs-based distributed feedback laser at 780 nm for 87Rb cold atom quantum technology. , 2017, , .		4
152	Faceting of Si and Ge crystals grown on deeply patterned Si substrates in the kinetic regime: phase-field modelling and experiments. <i>Scientific Reports</i> , 2021, 11, 18825.	3.3	4
153	Terahertz Plasma Field Effect Transistors. <i>Springer Series in Optical Sciences</i> , 2014, , 77-100.	0.7	4
154	High-efficiency Ge-on-Si SPADs for short-wave infrared. , 2019, , .		4
155	Si/SiGe n-type inverted modulation doping using ion implantation. <i>Thin Solid Films</i> , 2000, 369, 324-327.	1.8	3
156	Conductivity of weakly and strongly localized electrons in an-type Si/SiGe heterostructure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 67-70.	0.8	3
157	Terahertz Frequency Security Systems and Terahertz Safety Considerations. <i>Springer Series in Optical Sciences</i> , 2014, , 233-255.	0.7	3
158	Modelling and experimental verification of a Ge/SiGe thermoelectric generator. , 2015, , .		3
159	Specially designed solar cells for hybrid photovoltaic-thermal generators. , 2016, , .		3
160	Expanding the Ge emission wavelength to 2.25 μ m with SixNy strain engineering. <i>Thin Solid Films</i> , 2016, 602, 60-63.	1.8	3
161	Mid-infrared n-Ge on Si plasmonic based microbolometer sensors. , 2017, , .		3
162	Geiger Mode Ge-on-Si Single-Photon Avalanche Diode Detectors. , 2019, , .		3

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163	Low loss germanium-on-silicon waveguides for integrated mid-infrared photonics. , 2019, , .		3
164	Current leakage mechanisms related to threading dislocations in Ge-rich SiGe heterostructures grown on Si(001). Applied Physics Letters, 2021, 119, .	3.3	3
165	Fabrication of SiGe quantum devices by electron-beam induced damage. Superlattices and Microstructures, 1997, 21, 29-36.	3.1	2
166	Far-infrared cyclotron resonance study of the effect of strain and localisation in Si/SiGe two dimensional electron gases. Solid-State Electronics, 1998, 42, 1159-1163.	1.4	2
167	The relative performance enhancement of strained-Si and buried channel p-MOS as a function of lithographic and effective gate lengths. , 0, , .		2
168	Strained-Si n-MOS surface-channel and buried Si _{0.7} Ge _{0.3} compressively-strained p-MOS fabricated in a 0.25 μ m heterostructure CMOS process. Materials Science in Semiconductor Processing, 2005, 8, 343-346.	4.0	2
169	Electron effective mass enhancement in ultrathin gate-oxide Si-MOSFETs. AIP Conference Proceedings, 2005, , .	0.4	2
170	Strain-symmetrized Si/SiGe multi-quantum well structures grown by molecular beam epitaxy for intersubband engineering. Journal of Luminescence, 2006, 121, 403-408.	3.1	2
171	Doubling speed using strained Si/SiGe CMOS technology. Thin Solid Films, 2006, 508, 338-341.	1.8	2
172	SiGe/Si quantum cascade structures deposited by low-energy plasma-enhanced CVD. , 2008, , .		2
173	Si/SiGe bound-to-continuum quantum cascade terahertz emitters. Proceedings of SPIE, 2008, , .	0.8	2
174	Long Wavelength {greater than or equal to}1.9 μ m Germanium for Optoelectronics Using Process Induced Strain. ECS Transactions, 2013, 50, 779-782.	0.5	2
175	Si/SiGe Tunneling Static Random Access Memories. ECS Transactions, 2013, 50, 987-990.	0.5	2
176	Finite Element Modelling To Evaluate the Cross-plane Thermal conductivity and Seebeck Coefficient of Ge/SiGe Heterostructure. Materials Today: Proceedings, 2015, 2, 510-518.	1.8	2
177	Germanium plasmonic nanoantennas for third-harmonic generation in the mid infrared. , 2016, , .		2
178	Variability study of high current junctionless silicon nanowire transistors. , 2017, , .		2
179	Improved Light Incoupling in Planar Solar Cells via Improved Texture Morphology of PDMS Scattering Layer. , 2017, , .		2
180	Geiger Mode Ge-on-Si Single-Photon Avalanche Diode Detectors. , 2019, , .		2

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181	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. Crystal Growth and Design, 2020, 20, 2914-2920.	3.0	2
182	Structural and Compositional Properties of Strain-Symmetrized SiGe/Si Heterostructures. Springer Proceedings in Physics, 2008, , 269-272.	0.2	2
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